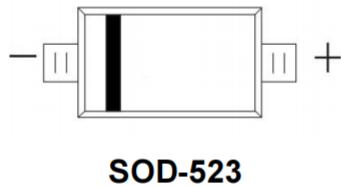


## Features

- Multilayer Metal -Silicon Potential Structure
- High Current Capability, High Efficiency
- High Junction Temperature Capability
- Low Leakage Current
- RoHs Product



## Applications

- Surface mount schottky barrier rectifier
- Buck and Boost dc-dc Converters
- Low Voltage High Frequency Switching Power Supply
- Low Voltage High Frequency Invers Circuit
- Low Voltage Continued Circuit and Protection Circuit



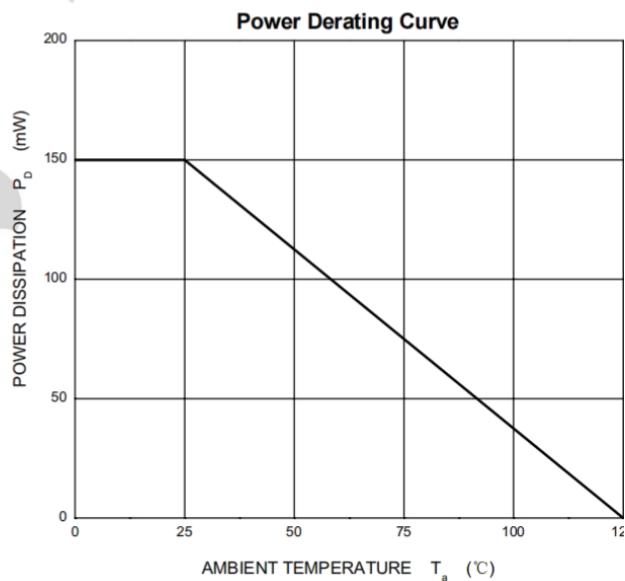
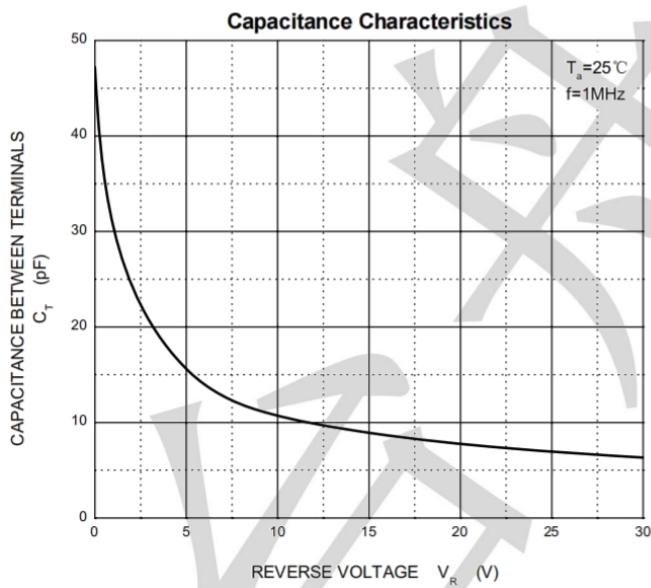
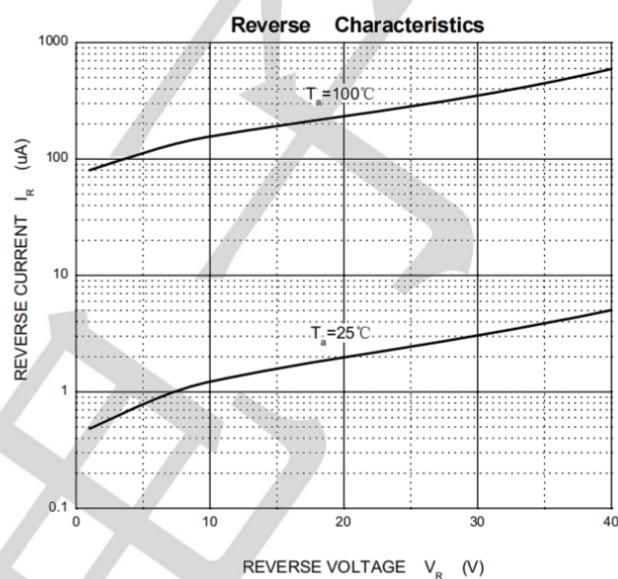
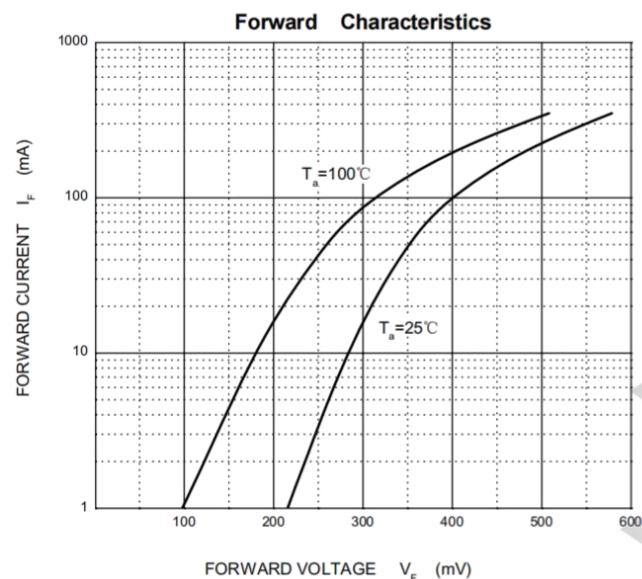
## Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Reverse Voltage	VR, VRM, VRWM	40	V
Maximum RMS voltage	VRMS	28	V
Forward Continuous Current	IFM	350	mA
Non-Repetitive Peak Forward Surge Current@t=8.3ms	IFSM	2.0	A
Power Dissipation	PD	150	mW
Typical Thermal Resistance per leg @TA = 25°C	RθJA	667	°C/W
Operating Junction Temperature Range	TJ	125	°C
Storage Temperature Range	TSTG	-55 to +150	°C

## Electrical Characteristics (TA=25°C unless otherwise specified)

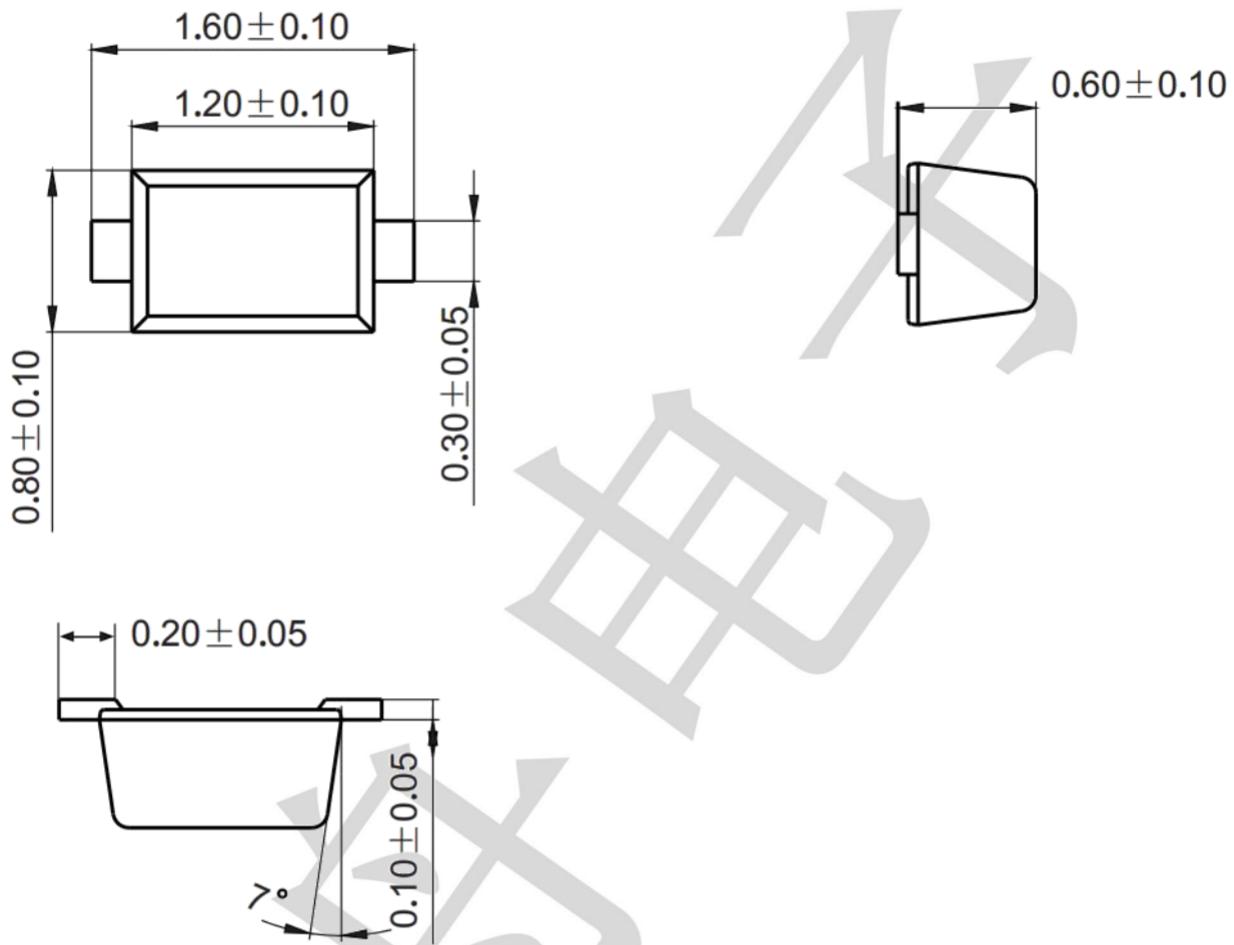
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse voltage	V <sub>(BR)</sub>	IF=100uA	40	--	--	V
Reverse current	I <sub>R</sub>	V <sub>R</sub> =30V	--	--	5	uA
		V <sub>R</sub> =20V	--	--	2	uA
		V <sub>R</sub> =10V	--	--	1	uA
Forward voltage	V <sub>F</sub>	IF=1mA	--	0.27	--	V
		IF=5mA	--	0.32	--	V
		IF=20mA	--	--	0.37	V
		IF=200mA	--	--	0.6	V
Total Capacitance	C <sub>tot</sub>	VR = 0 V, f = 1 MHz	--	50	--	pF
Reverse recovery time	t <sub>rr</sub>	IF= I <sub>R</sub> =200mA, I <sub>rr</sub> =0.1×I <sub>R</sub> , R <sub>L</sub> =100Ω	--	10	--	ns

### Typical Electrical Characteristic Curves



**Package Outline Dimensions (unit: mm)**

SOD-523



**Mounting Pad Layout (unit: mm)**

